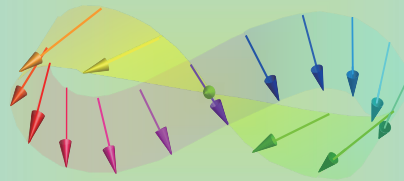


Nanoelectronics

15



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10:00 Monday, 06/March/2023 (P/L 006)



Quick Review over the Last Lecture

	Fermi-Dirac distribution	Bose-Einstein distribution
Function		
Energy dependence		
Quantum particles		
Spins		
Properties	At temperature of 0 K, each energy level is occupied by two Fermi particles with opposite spins. →	At very low temperature, large numbers of Bosons fall into the lowest energy state. →



Contents of Nanoelectronics

- I. Introduction to Nanoelectronics (01)
 - 01 Micro- or nano-electronics ?
- II. Electromagnetism (02 & 03)
 - 02 Maxwell equations
 - 03 Scalar and vector potentials
- III. Basics of quantum mechanics (04 ~ 06)
 - 04 History of quantum mechanics 1
 - 05 History of quantum mechanics 2
 - 06 Schrödinger equation
- IV. Applications of quantum mechanics (07, 10, 11, 13 & 14)
 - 07 Quantum well
 - 10 Harmonic oscillator
 - 11 Magnetic spin
 - 13 Quantum statistics 1
 - 14 Quantum statistics 2
- V. Nanodevices (08, 09, 12, 15 ~ 18)
 - 08 Tunnelling nanodevices
 - 09 Nanomeasurements
 - 12 Spintronic nanodevices
 - 15 Low-dimensional nanodevices

15 Low-Dimensional Nanodevices

- Quantum wells
 - Superlattices
- 2-dimensional electron gas
 - Quantum nano-wires
 - Quantum dots



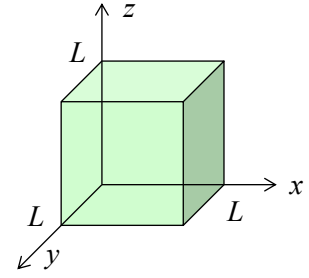
Schrödinger Equation in a 3D Cube

In a 3D cubic system, Schrödinger equation for an inside particle is written as :

$$\frac{\hbar^2}{2m} \left(\frac{\partial^2}{\partial x^2} + \frac{\partial^2}{\partial y^2} + \frac{\partial^2}{\partial z^2} \right) \psi(x,y,z) + (E - V)\psi(x,y,z) = 0$$

where a potential is defined as

$$V = \begin{cases} 0 & (\text{inside the box : } 0 \leq x \leq L, 0 \leq y \leq L, 0 \leq z \leq L) \\ +\infty & (\text{outside the box : } x,y,z < 0, x,y,z > L) \end{cases}$$



By considering the space symmetry, the wavefunction is

$$\psi(\mathbf{r}, t) = \psi(x, t)\psi(y, t)\psi(z, t)$$

Inside the box, the Schrödinger equation is rewritten as

$$-\frac{\hbar^2}{2m} \left(\frac{\partial^2}{\partial x^2} + \frac{\partial^2}{\partial y^2} + \frac{\partial^2}{\partial z^2} \right) \psi(x, t)\psi(y, t)\psi(z, t) = E\psi(x, t)\psi(y, t)\psi(z, t)$$

$$-\frac{\hbar^2}{2m} \left(\frac{1}{\psi(x, t)} \frac{\partial^2}{\partial x^2} \psi(x, t) + \frac{1}{\psi(y, t)} \frac{\partial^2}{\partial y^2} \psi(y, t) + \frac{1}{\psi(z, t)} \frac{\partial^2}{\partial z^2} \psi(z, t) \right) = E_x + E_y + E_z$$

In order to satisfy this equation, 1D equations need to be solved :

$$-\frac{\hbar^2}{2m} \frac{\partial^2}{\partial x^2} \psi(x, t) = E_x \psi(x, t)$$



Schrödinger Equation in a 3D Cube (Cont'd)

To solve this 1D Schrödinger equation, $-\frac{\hbar^2}{2m} \frac{\partial^2}{\partial x^2} \psi(x, t) = E_x \psi(x, t)$,

we assume the following wavefunction, $\psi(x, t) = \phi(x)\exp(-i\omega t)$, and substitute into the above equation :

$$-\frac{\hbar^2}{2m} \frac{\partial^2}{\partial x^2} \phi(x)\exp(-i\omega t) = E_x \phi(x)\exp(-i\omega t)$$

By dividing both sides with $\exp(-i\omega t)$,

$$-\frac{\hbar^2}{2m} \frac{\partial^2}{\partial x^2} \phi(x) = E_x \phi(x) \rightarrow$$

By substituting into the steady-state Schrödinger equation,

$$k_x = \pm \frac{\sqrt{2mE_x}}{\hbar}$$

For $0 \leq x \leq L$, a general solution can be defined as

$$\phi(x) = A\sin(k_x x) + B\cos(k_x x)$$

At $x = 0$, the probability of the particle is 0, resulting $\phi(0) = 0 : B = 0$.

Similarly, $\phi(L) = 0 : k_x = \frac{n_x \pi}{L}$ ($n_x = 1, 2, 3, \dots$)



Schrödinger Equation in a 3D Cube (Cont'd)

By normalising $\phi(x) = A \sin\left(\frac{n_x \pi}{L} x\right)$,

$$\therefore A = \sqrt{\frac{2}{L}}$$

Hence, the wave function on x is obtained as

$$\phi(x) = \left(k_x = \frac{\sqrt{2mE_x}}{\hbar} \right)$$

By considering the symmetry, a particle in a 3D cubic system can be described with the wavefunction :

$$\psi(x, y, z) = \psi(x, t)\psi(y, t)\psi(z, t) = \left(\right)^{\frac{3}{2}}$$

Here, the energy eigen values are

$$E = \frac{\hbar^2}{2m} \left(\right) = \frac{\hbar^2}{2m} \left(\right)^2 \left(\right) \\ (n_x, n_y, n_z = 1, 2, 3, \dots)$$



Density of States in Low-Dimensions

The available states can be obtained as

$$n_x^2 + n_y^2 + n_z^2 = \frac{2m}{\hbar^2} \left(\frac{L}{\pi}\right)^2 E$$

The available states can be approximated by the volume of the Fermi sphere ($x, y, z \geq 0$) :

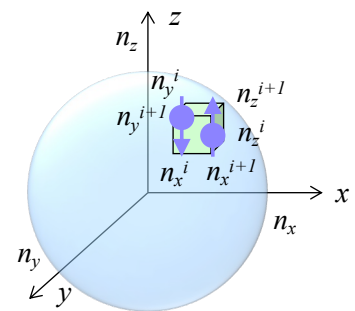
$$N^2 = \frac{1}{8} \frac{4\pi}{3} \left(\sqrt{\frac{2m}{\hbar^2} \left(\frac{L}{\pi}\right)^2 E} \right)^3 = \frac{L^3}{6\pi^2} \left(\frac{2m}{\hbar^2}\right)^{3/2} E^{3/2}$$

By dividing both sides by L^3 :

$$N(E) = \frac{1}{6\pi^2} \left(\frac{2m}{\hbar^2}\right)^{3/2} E^{3/2} \left[= \right]$$

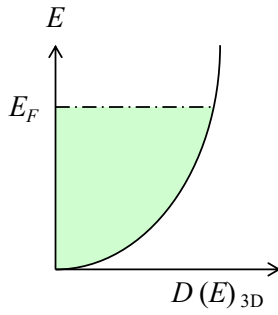
The density of states can be obtained as :

$$D(E) = \frac{dN}{dE} = \frac{2}{3\pi^2} \left(\frac{2m}{\hbar^2}\right)^{3/2}$$

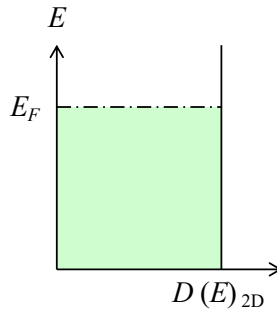




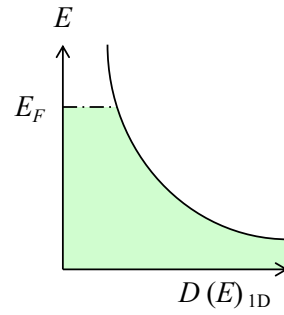
Density of States in Low-Dimensions



$$D(E)_{3D} \propto E^2$$



$$D(E)_{2D} \propto \text{constant}$$



$$D(E)_{1D} \propto E^{-1/2}$$

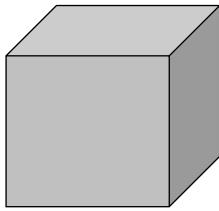
→ Anderson localisation



Dimensions of Nanodevices

By reducing the size of devices,

3D :



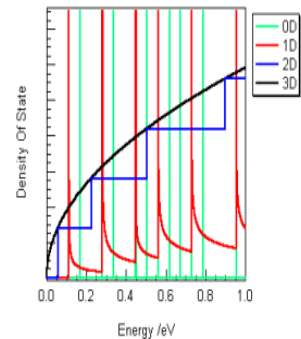
2D :



1D :



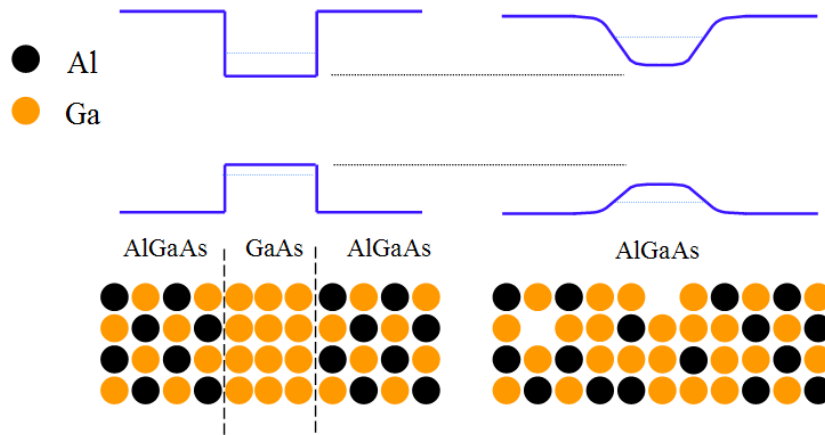
0D :





Quantum Well

A layer (thickness $<$) is sandwiched by high potentials :

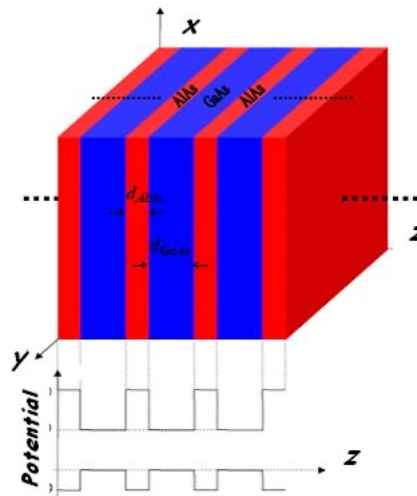


* <http://www.intenseco.com/technology/>



Superlattice

By employing ultrahigh vacuum molecular-beam epitaxy and sputtering growth, periodically alternated layers of several substances can be fabricated :

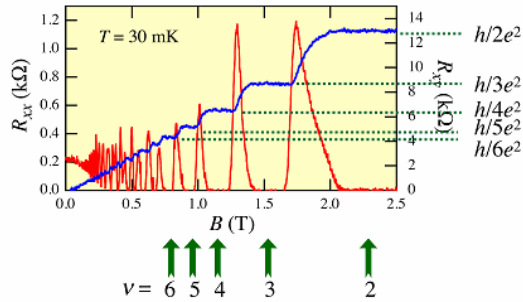


* <http://www.wikipedia.org/>



Quantum Hall Effect

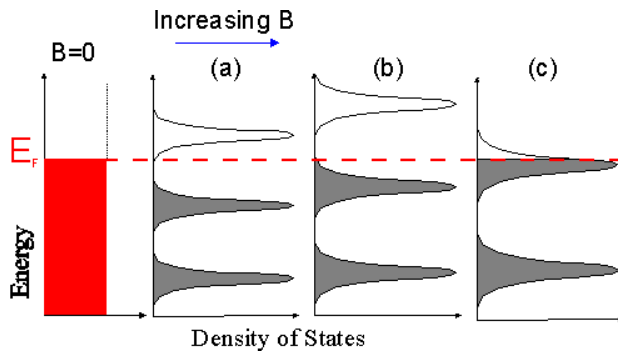
First experimental observation was performed by Klaus von Klitzing in 1980 :



By increasing a magnetic field, the Fermi level in 2DEG changes.

This was theoretically proposed by Tsuneya Ando in 1974 :

→ Observation of the Landau levels.

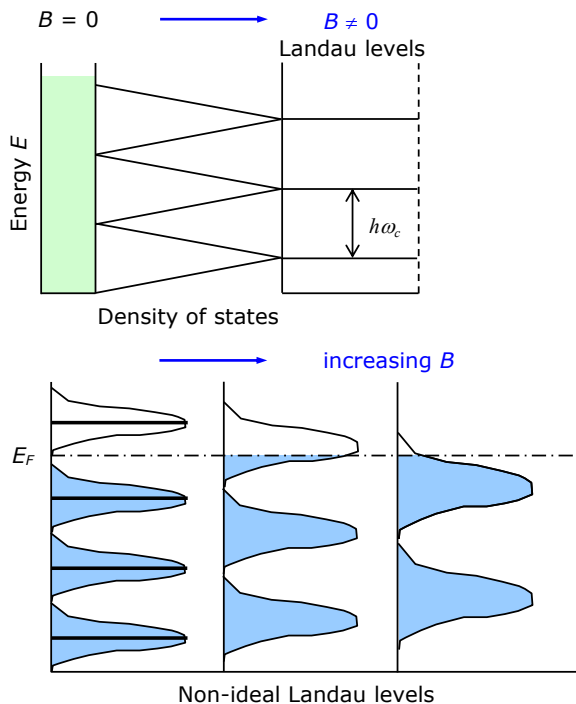


- * <http://www.wikipedia.org/>
- ** <http://qhe.iis.u-tokyo.ac.jp/research7.html>
- *** <http://www.stat.phys.titech.ac.jp/ando/>
- † <http://www.warwick.ac.uk/~phsbn/qhe.htm>



Landau Levels

Lev D. Landau proposed quantised levels under a strong magnetic field :

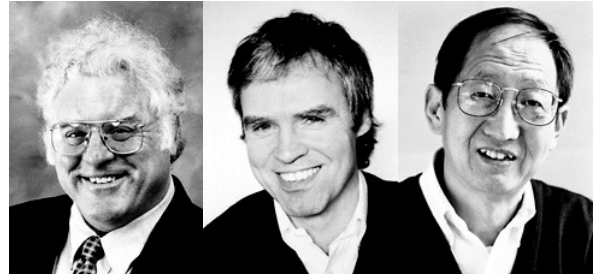
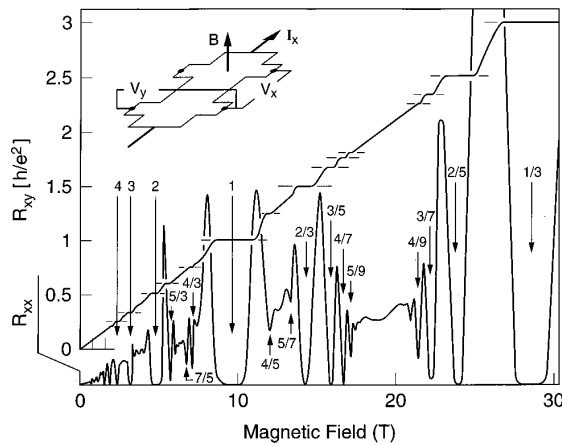


* <http://www.wikipedia.org/>



Fractional Quantum Hall Effect

In 1982, the fractional quantum Hall effect was discovered by Robert B. Laughlin, Horst L. Strömer and Daniel C. Tsui :



Coulomb interaction between electrons > Quantised potential
← Improved quality of samples (less impurity)

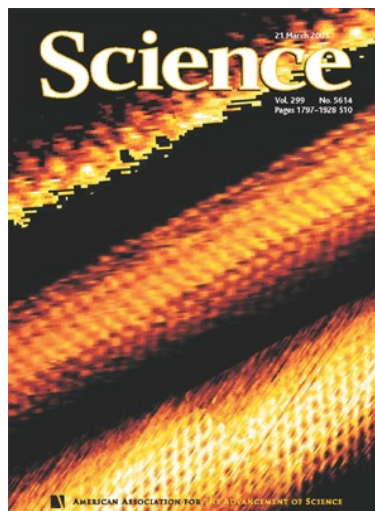
* <http://nobelprize.org/>

** H. L. Strömer *et al.*, *Rev. Mod. Phys.* **71**, S298 (1999).



Quantum Nano-Wire

By further reducing another dimension, ballistic transport can be achieved :

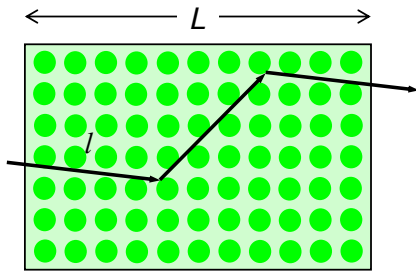


* D. D. D. Ma *et al.*, *Science* **299**, 1874 (2003).



Diffusive / Ballistic Transport

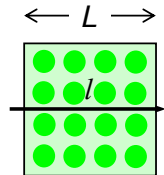
In a macroscopic system, electrons are scattered :



System length (L) > Mean free path (l)

→ transport

When the transport distance is smaller than the mean free path,



System length (L) \leq Mean free path (l)

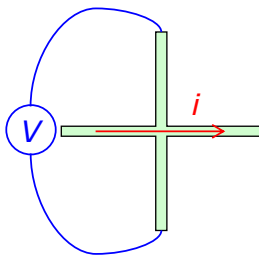
→ transport



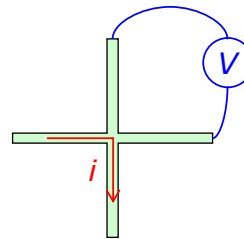
Resistance-Measurement Configurations

In a nano-wire device, 4 major configurations are used to measure resistance :

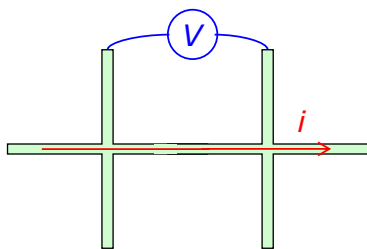
Hall resistance :



Bend resistance :

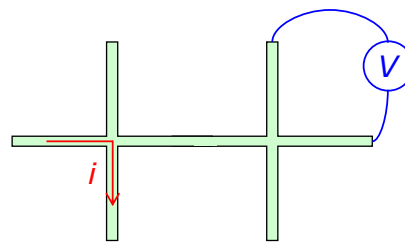


Longitudinal resistance :



method

Transmission resistance :

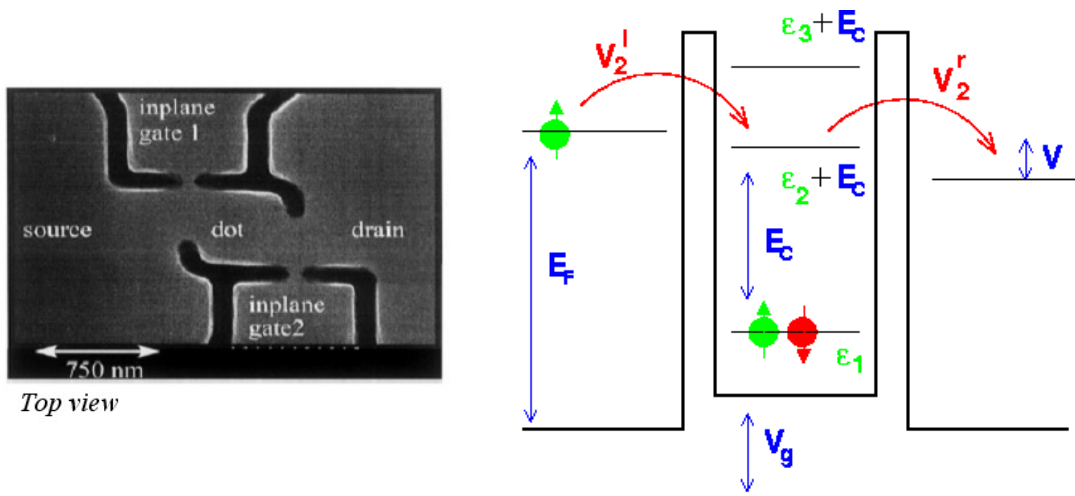


method



Quantum Dot

By further reduction in a dimension, well-controlled electron transport is achieved :



* <http://www.fkf.mpg.de/metzner/research/qdot/qdot.html>



Nanofabrication - Photolithography

Photolithography :

Typical wavelength :

Hg lamp (g-line: 436 nm and i-line: 365 nm),
KrF laser (248 nm) and ArF laser (193 nm)

Resolution : > 50 nm (KrF / ArF laser)

Typical procedures :

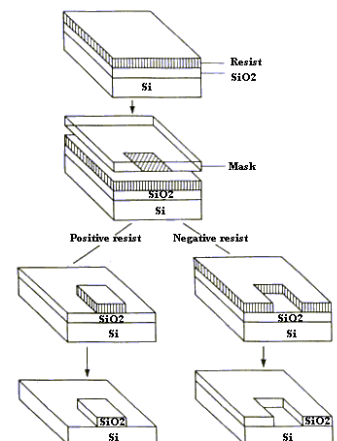
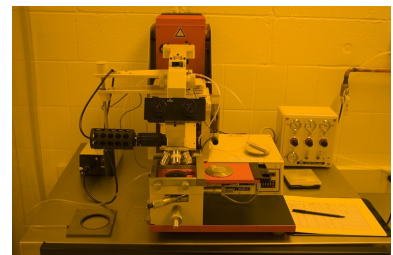
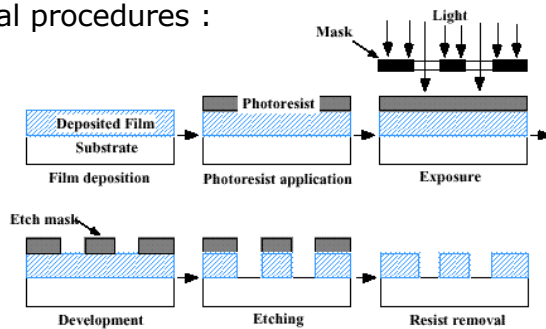


Photo-resists :

negative-type (SAL-601, AZ-PN-100, etc.)
positive-type (PMMA, ZEP-520, MMA, etc.)

* <http://www.wikipedia.org/>

** <http://www.hitequest.com/Kiss/VLSI.htm>

*** <http://www.ece.gatech.edu/research/labs/vc/theory/photolith.html>

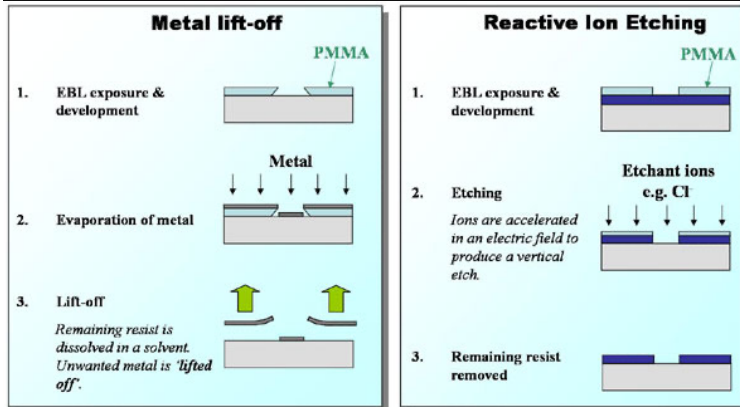
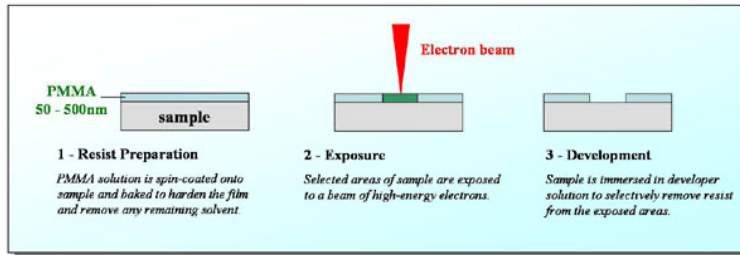


Nanofabrication - Electron-Beam Lithography

Electron-beam lithography :

Resolution : < 10 nm

Typical procedures :

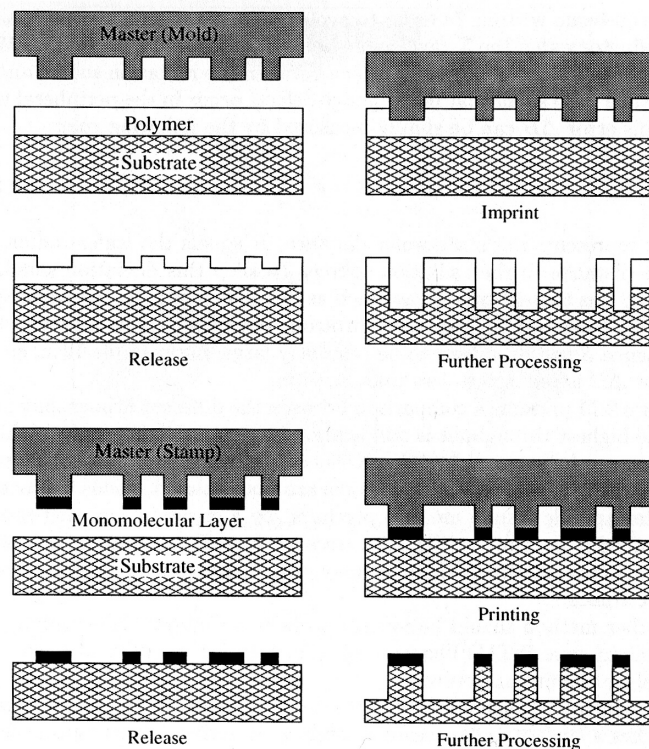
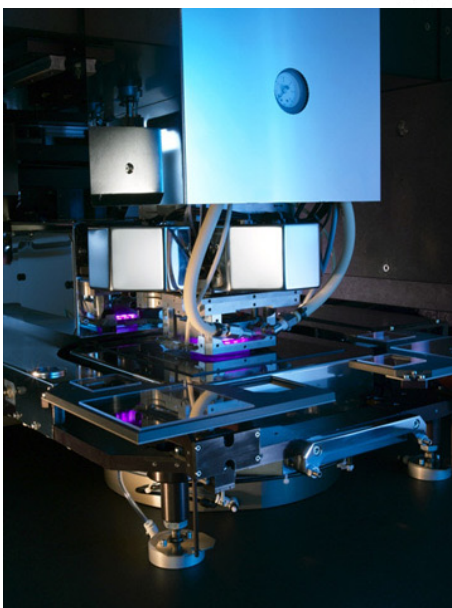


* <http://www.shef.ac.uk/eee/research/eb1/principles.html>



Nanofabrication

Nano-imprint :



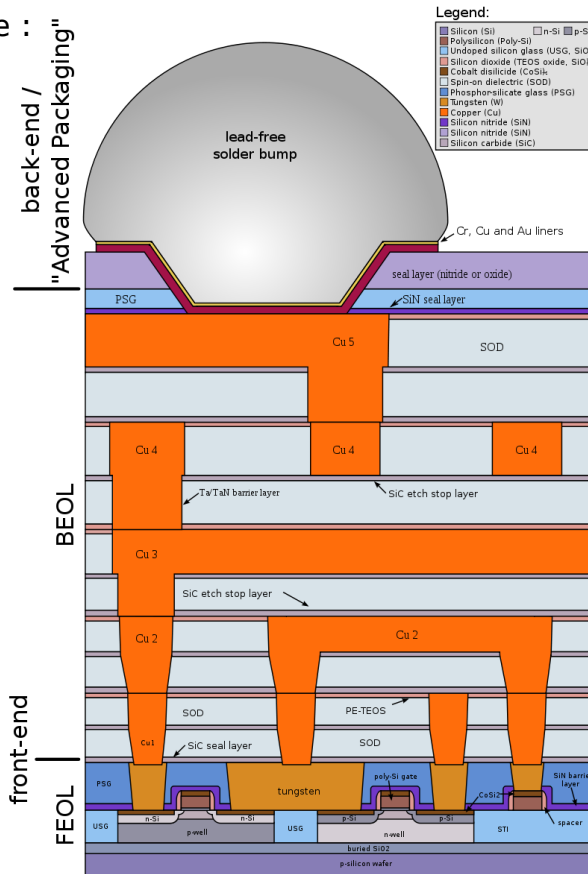
* <http://www.leb.eei.uni-erlangen.de/reinraumlabor/ausstattung/strukturierung.php?lang=en>

** K. Gosser, P. Glosekotter and J. Diestuhl, *Nanoelectronics and Nanosystems* (Springer, Berlin, 2004).



Current Process Technology

Front / back end of line :



* <http://www.wikipedia.org/>



Next-Generation Nanofabrication

Development of nanofabrication techniques :

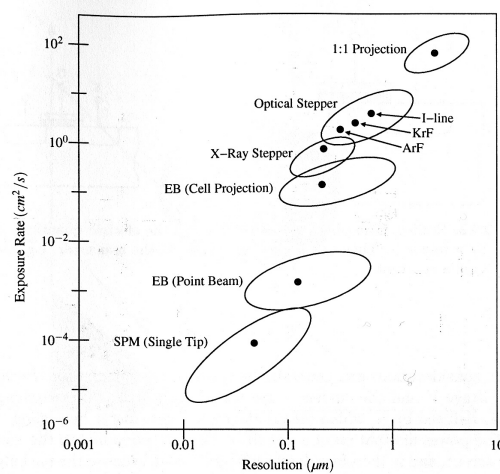


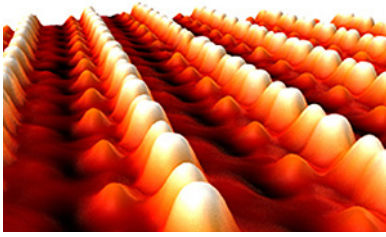
Fig. 2.11. Comparison of different lithography techniques from the production point of view



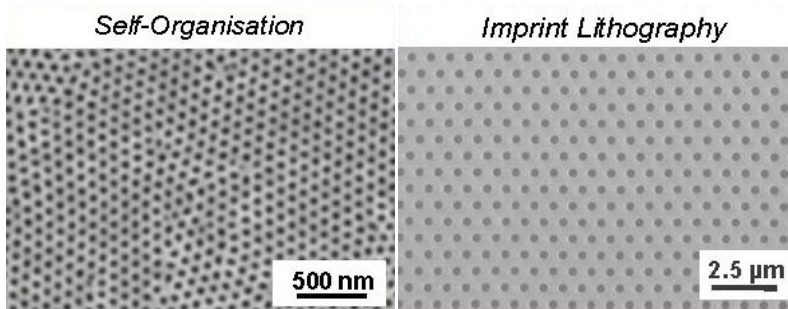
Bottom Up Technology

Self-organisation (self-assembly) without any control :

Pt nano-wires



Polymer



* <http://www.omicron.de/>

** <http://www.nanomikado.de/projects.html>